CLAIMS

1. An abrasive construction for use in chemical mechanical polishing of a substrate including at least one conducting or semiconducting layer, wherein the abrasive construction comprises at least one abrasion-effective layer adapted to remove at least a portion of the conducting or semiconducting layer from the substrate, the abrasion-effective layer comprising at least one solid oxidant.

2. The abrasive construction of claim 1, wherein said oxidant is selected from the group of halogen derivatives, organic nitro compounds, copper oxides or salts thereof and mixtures thereof.

3. The construction of claim 1 wherein said abrasion-effective layer further comprises a surfactant.

4. The construction of claim 1, wherein said abrasion-effective layer further comprises a complexing agent.

5. The construction of claim 1, comprising multiple abrasion-effective layers.

6. A method for polishing a substrate including at least one conducting or semiconducting layer, the method comprising bringing the construction of claim 1 into contact with the substrate, moving the construction in relation to the substrate and removing at least a portion of the conducting or semiconducting layer from the substrate.

7. The method of claim 1 further comprising a conditioning step of said at least one abrasion-effective layer prior to, or during its contact with the substrate,

said conditioning step comprising contacting said abrasion-effective layer with an organic solvent, an emulsion , a microemulsion or buffered aqueous solution.